wherein edge portions of said active layer and a part of edge portion of said wirings are aligned, and

wherein the gate insulating film is not in contact with the insulating surface.

2. (Amended) A liquid crystal display device having a plurality of thin film transistors, at least one of said thin film transistors comprising:

an active layer having a source and drain regions over an insulating surface;

a gate insulating film over said active layer;

a gate electrode over said gate insulating film; and

two wirings connected to said source and drain regions, each of said wirings electrically connecting one of said plurality of thin film transistors,

wherein edge portions of said active layer and a part of edge portion of said wirings are aligned, and

wherein the gate insulating film is not in contact with the insulating surface.

Please add new claims 21-31 as follows:

--21. A liquid crystal display device having a plurality of thin film transistors, at least one of said thin film transistors comprising:

an active layer over an insulating surface;

a gate insulating film over said active layer;

a gate electrode over said gate insulating film; and

two wirings connected to said active layer, each of said wirings electrically connecting one of said plurality of thin film transistors,

wherein a part of an edge portion of at least one of two wirings is aligned with at least one edge portion of the active layer, and

wherein the gate insulating film is not in contact with the insulating surface.

22. A semiconductor device comprising:

at least one thin film transistor comprising:

an active layer over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of at least one of two wirings is aligned with at least one edge portion of the active layer, and

wherein the insulating film is in contact with the insulating surface.

B2 cont.

23. A semiconductor device comprising:

at least one thin film transistor comprising:

an active layer over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of one of the first and second wirings is aligned with an edge of the active layer, and

wherein the insulating film is in contact with the insulating surface.

24. A semiconductor device comprising:

at least one thin film transistor comprising:

an active layer over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of the first wiring is aligned with one of edge portions of the active layer, and a part of an edge portion of the second wiring is aligned with another one of edge portions of the active layer, and

wherein the second insulating film is in contact with the insulating surface.

25. A semiconductor device according to claim 21, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

26. A semiconductor device according to claim 22, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

27. A semiconductor device according to claim 23, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

28. A semiconductor device according to claim 24, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, an rear projector and a front projector.

29. A semiconductor device according to claim 22, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

B2 30. A semiconductor device according to claim 23, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

31. A semiconductor device according to claim 24, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide. --